

The Influence of Argon Cluster Ion Bombardment on the Characteristics of AlN films on Glass-Ceramics and Si Substrates

Ivan V. Nikolaev ^{1,2,*}, Pavel V. Geydt ^{1,*}, Nikolay G. Korobeishchikov ², Aleksandr V. Kapishnikov ^{1,3}, Vladimir A. Volodin ^{1,4}, Ivan A. Azarov ^{1,4}, Vladimir I. Strunin ^{5,6} and Evgeny Y. Gerasimov ³

¹ Laboratory of Functional Diagnostics of Low-dimensional Structures for Nanoelectronics, Novosibirsk State University, Novosibirsk 630090, Russia; a.kapishnikov@nsu.ru (A.V.K.); v.volodin@nsu.ru (V.A.V.); i.azarov@nsu.ru (I.A.A.)

² Department of Applied Physics, Novosibirsk State University, Novosibirsk 630090, Russia; korobei@nsu.ru

³ Boreskov Institute of Catalysis, Russian Academy of Sciences (Siberian Branch), Novosibirsk 630090, Russia; gerasimov@catalysis.ru

⁴ Rzhzanov Institute of Semiconductor Physics, Russian Academy of Sciences (Siberian Branch), Novosibirsk 630090, Russia

⁵ Department of Experimental Physics and Radiophysics, Dostoevsky Omsk State University, Omsk 644077, Russia; struninvi@omsu.ru

⁶ Institute of Radiophysics and Physical Electronics, Omsk Scientific Center, Russian Academy of Sciences (Siberian Branch), Omsk 644024, Russia

* Correspondence: i.nikolaev@nsu.ru (I.V.N.); p.geydt@nsu.ru (P.V.G.)

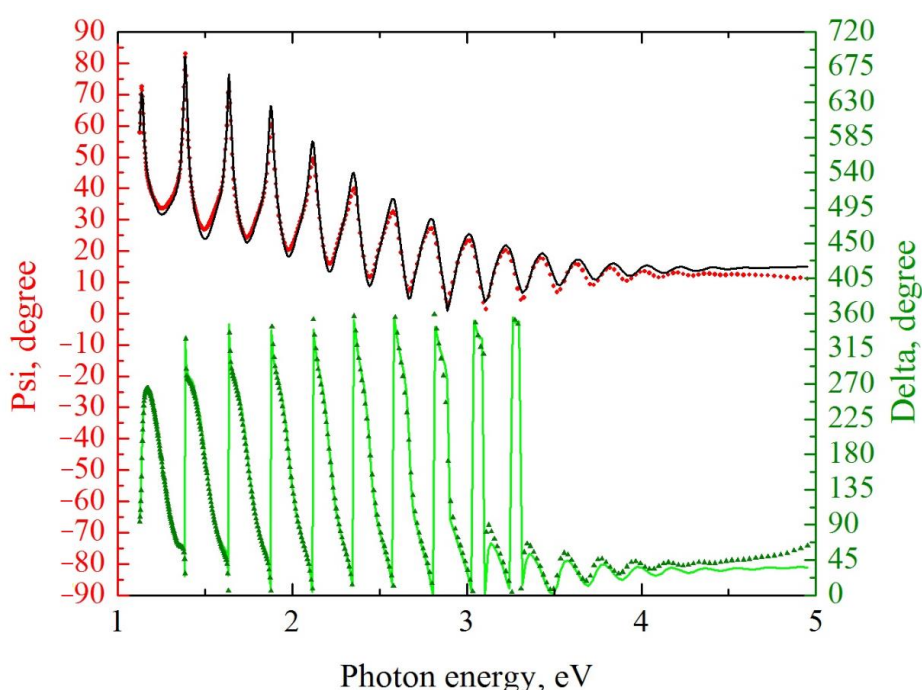


Figure S1. Results of ellipsometry multilayer model.